

Amendments to the Claims: Claims 1 and 14 are amended. No claims have been added or canceled. Therefore claims 1-7, 9-10, 14-18, 20, 22-28 remain pending.

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A method comprising:  
disposing a trench layer upon a semiconductor substrate;  
forming one or more trenches in the trench layer exposing the semiconductor substrate;  
filling the one or more trenches with a semiconductor material contacting the semiconductor substrate; and  
removing a portion of the trench layer to expose the semiconductor material as one or more semiconductor fins.
2. (Original) The method of claim 1 wherein the trench layer is comprised of a plurality of layers.
3. (Original) The method of claim 2 wherein the plurality of layers include a first oxide layer disposed upon the semiconductor substrate, a nitride layer disposed upon the first oxide layer, and a second oxide layer disposed upon the nitride layer.
4. (Original) The method of claim 3 wherein removing an additional portion of the trench layer comprises removing any remaining portion of the second oxide layer, any remaining portion of the nitride layer, and retaining at least some portion of any remaining portion of the first oxide layer.
5. (Original) The method of claim 1 wherein the one or more trenches have a depth of approximately 10 nm.
6. (Original) The method of claim 5 wherein the one or more semiconductor fins have a height of approximately 10 nm that is uniform to within 5%.

7. (Previously Presented) The method of claim 1, further comprising:  
planarizing the semiconductor material to a surface of the trench layer prior to exposing the semiconductor material as one or more semiconductor fins.
8. (Canceled)
9. (Original) The method of claim 1 wherein filling the one or more trenches with a semiconductor material includes epitaxially growing the semiconductor material within the one or more trenches.
10. (Original) The method of claim 1 wherein filling the one or more trenches with a semiconductor material includes a blanket deposition of semiconductor material.
11. - 13. (Canceled)
14. (Currently Amended) A method comprising:  
disposing a first oxide layer on a semiconductor substrate;  
disposing a nitride layer upon the first oxide layer;  
disposing a second oxide layer upon the nitride layer;  
selectively etching a portion of the second oxide layer, the nitride layer and the first oxide layer defining one or more trenches;  
filling the one or more trenches with a semiconductor material contacting said semiconductor substrate; and  
selectively etching a remainder of the second oxide layer such that one or more semiconductor bodies are formed from the semiconductor material.
15. (Original) The method of claim 14 wherein the one or more trenches have a depth of approximately 10 nm.
16. (Original) The method of claim 14 wherein the one or more semiconductor bodies have a height of less than 20 nm that is uniform to within 5%.

17. (Original) The method of claim 16 wherein the one or more semiconductor bodies have a height of approximately 10 nm.
18. (Previously Presented) The method of claim 14 further comprising:  
planarizing the semiconductor material to a surface of the second oxide layer.
19. (Canceled)
20. (Original) The method of claim 14 wherein filling the one or more trenches with a semiconductor material includes epitaxially growing the semiconductor material within the one or more trenches.
21. (Canceled)
22. (Original) The method of claim 14 wherein the semiconductor substrate is comprised of a semiconductor material selected from the group consisting of silicon, germanium, and gallium arsenide.
23. (Original) The method of claim 14 wherein the semiconductor substrate is comprised of silicon, the first oxide layer is comprised of  $\text{SiO}_2$ , the nitride layer is comprised of  $\text{Si}_3\text{N}_4$ , and the second oxide layer is comprised of  $\text{SiO}_2$ .
24. (Previously Presented) A method comprising:  
forming a first film over a semiconductor substrate;  
forming a second film on said first film;  
forming a trench in said first film and said second film and exposing the semiconductor substrate;  
forming an epitaxial semiconductor film in said trench; and  
exposing a sidewall of said semiconductor film by removing said second film selectively from said first film.
25. (Previously Presented) The method in claim 24, further comprising:

forming a gate dielectric on said sidewall of said semiconductor film;  
forming a gate electrode on said gate dielectric; and  
forming a source and drain region in said semiconductor film on opposite sides of said gate electrode.

26. (Previously Presented) The method in claim 24, wherein said first film is a silicon nitride and said second film is a silicon oxide.

27. (Previously Presented) The method in claim 24, wherein said first film is a silicon oxide and said second film is a silicon nitride.

28. (Previously Presented) The method in claim 24, further comprising:  
removing any excess semiconductor material from said trench prior to exposing a sidewall of said semiconductor film.

29. - 30. (Canceled)